



30V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C	
2014	2.2mΩ @ V _{GS} = 10V	170A	
30V	$3.2m\Omega$ @ $V_{GS} = 4.5V$	140A	

Description and Applications

PowerDI5060-8

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Features

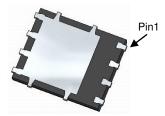
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (Test in Production) Ensures More Reliable and Robust End Application
- <1.1mm Package Profile Ideal for Thin Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

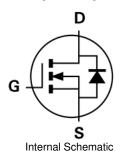
- Case: PowerDI[®] 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202. Method 208 (3)
- Weight: 0.097 grams (Approximate)

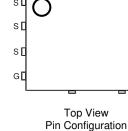






Bottom View





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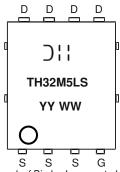
Ordering Information (Note 4)

Part Number	Case	Packaging	
DMTH32M5LPSQ-13	PowerDI5060-8	2,500 / Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



J;| = Manufacturer's Marking
TH32M5LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 18 = 2018)
WW = Week (01 to 53)



Maximum Ratings (@T_C = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±16	V
Continuous Drain Current, $V_{GS} = 10V$ (Note 7) Steady $T_C = +25^{\circ}C$ State $T_C = +100^{\circ}C$		Ι _D	170 120	Α	
Maximum Continuous Body Diode Forward Current (Note 7)			Is	80	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	350	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	350	Α
Avalanche Current, L = 0.1mH			I _{AS}	50	Α
Avalanche Energy, L = 0.1mH			Eas	140	mJ

Thermal Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P_{D}	3.2	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{ hetaJA}$	54	°C/W
Total Power Dissipation (Note 7)	$T_C = +25^{\circ}C$	P_{D}	100	W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	1.5	°C/W
Operating and Storage Temperature Range		T_J,T_STG	-55 to +175	°C

Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

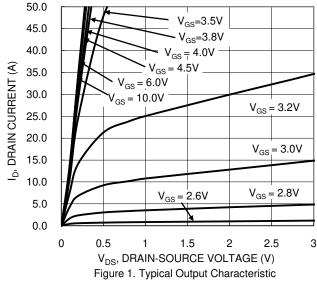
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)			- 71	111627	• • • • • • • • • • • • • • • • • • • •		
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	V _{GS} = 0V, I _D = 250μA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	V _{DS} = 24V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(TH)}$	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 1mA$	
Static Drain-Source On-Resistance		_	1.6	2.2	mΩ	$V_{GS} = 10V, I_D = 30A$	
Static Dialif-Source Off-Nesistatice	R _{DS(ON)}	_	2.6	3.2	11122	$V_{GS} = 4.5V, I_D = 30A$	
Diode Forward Voltage	V_{SD}	_	0.8	1.1	V	$V_{GS} = 0V, I_S = 30A$	
DYNAMIC CHARACTERISTICS (Note 9)	<u>.</u>					•	
Input Capacitance	C _{iss}	_	3944	_		V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	1267	_	рF		
Reverse Transfer Capacitance	C _{rss}	_	186	_			
Gate Resistance	Rg	_	0.6	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	34	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	68	_	nC	V 45V L 00A	
Gate-Source Charge	Q_{gs}	_	8	_	IIC	$V_{DS} = 15V, I_D = 20A$	
Gate-Drain Charge	Q_{gd}	_	15	_			
Turn-On Delay Time	t _{D(ON)}	_	7.2	_			
Turn-On Rise Time	t _R	_	13.2	_		$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	37.5	_	ns	$I_D = 15A$, $R_q = 3\Omega$	
Turn-Off Fall Time	t⊧	_	23.9	_		-	
Body Diode Reverse Recovery Time	t _{RR}	_	28.7	_	ns	1 15A di/d+ 500A/vc	
Body Diode Reverse Recovery Charge	Q _{RR}	_	45.8	_	nC	$I_S = 15A$, di/dt = 500A/ μ s	

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.7. Thermal resistance from junction to soldering point (on the exposed drain pad).8. Short duration pulse test used to minimize self-heating effect.

- 9. Guaranteed by design. Not subject to production testing.







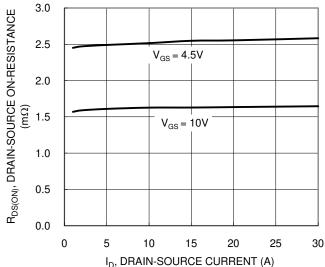


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

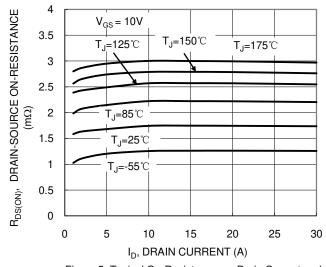


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

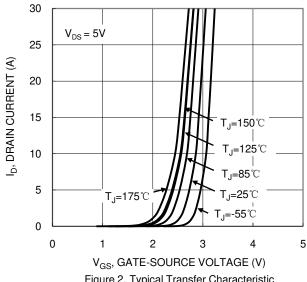


Figure 2. Typical Transfer Characteristic

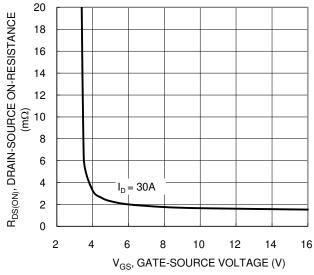


Figure 4. Typical Transfer Characteristic

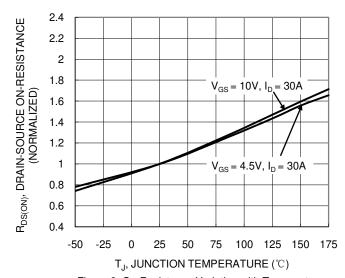


Figure 6. On-Resistance Variation with Temperature





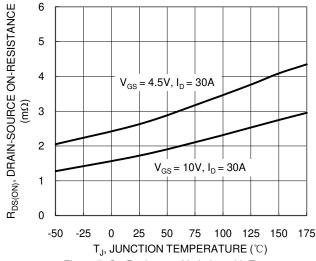


Figure 7. On-Resistance Variation with Temperature

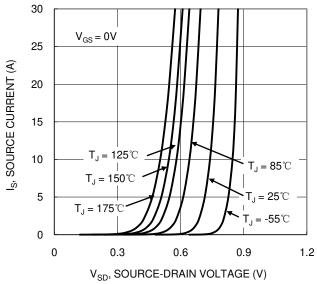


Figure 9. Diode Forward Voltage vs. Current

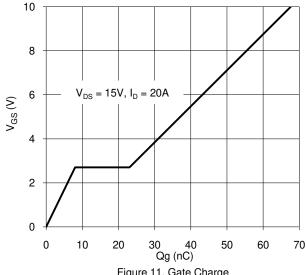


Figure 11. Gate Charge

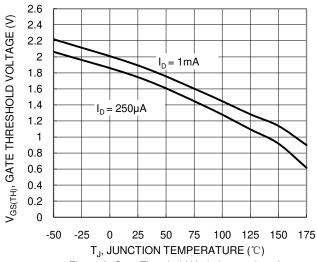


Figure 8. Gate Threshold Variation vs. Junction Temperature

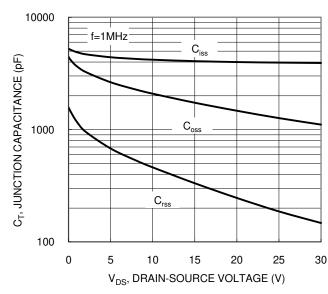
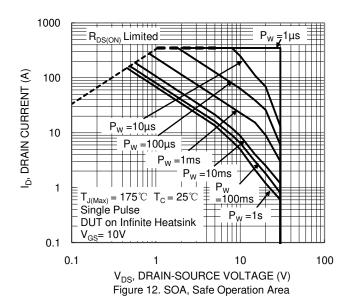


Figure 10. Typical Junction Capacitance





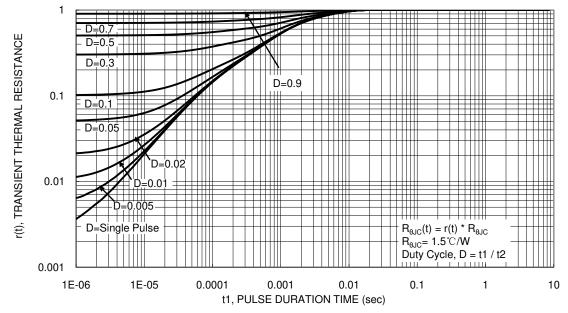


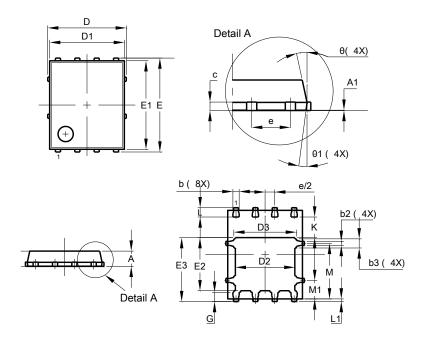
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

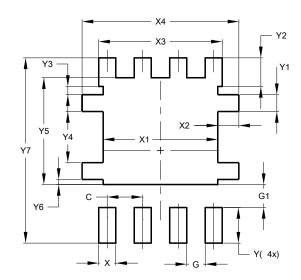


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	,	5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(6.15 BSC	;		
E1	5.60	5.60 6.00			
E2	3.28	3.68	3.48		
E3	3.99 4.39 4.1		4.19		
е		1.27 BSC			
G	0.51	0.71	0.61		
K	0.51	-	_		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)			
C	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y 7	6.610			



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